



DMP45H4D9HK3

#### **Product Summary**

BV <sub>DSS</sub>	RDS(ON) Max	Ι <sub>D</sub> T <sub>C</sub> = +25°C
-450V	4.9Ω @ V <sub>GS</sub> = -10V	-4.7A

## Description

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

# Applications

- Motor Control
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

#### 450V P-CHANNEL ENHANCEMENT MODE MOSFET

#### Features

- Low Input Capacitance
- High BV<sub>DSS</sub> Rating for Power Application
- Low Input/Output Leakage
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

#### **Mechanical Data**

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 <sup>(3)</sup>

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Internal Schematic

Weight: 0.33 grams (Approximate)



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Ordering Information (Note 4)

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Part Number	Case	Packaging
DMP45H4D9HK3-13	TO252 (DPAK)	2,500/Tape & Reel

Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

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3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### **Marking Information**



 $\begin{array}{l} \bigcirc | \ | \ = \ Manufacturer's \ Marking \\ 45H4D9 = \ Product \ Type \ Marking \ Code \\ \curlyvee WW = \ Date \ Code \ Marking \\ \Upsilon Y \ or \ \underline{YY} = \ Last \ Two \ Digits \ of \ Year \ (ex: \ 17 = 2017) \\ WW \ or \ \underline{WW} = \ Week \ Code \ (01 \ to \ 53) \end{array}$ 



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	-450	V
Gate-Source Voltage	V <sub>GSS</sub>	±30	V		
Continuous Drain Current (Note 5) $V_{GS} = -10V$	ID	-4.7 -3.0	A		
Maximum Body Diode Forward Current (Note 5)			Is	-1.5	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	-4.5	A
Avalanche Current, L = 60mH (Note 7)			I <sub>AS</sub>	-2.5	A
Avalanche Energy, L = 60mH (Note 7)			E <sub>AS</sub>	187	mJ

#### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 5)	$T_{\rm C} = +25^{\circ}{\rm C}$	Р	104	W	
Total Power Dissipation (Note 5)	T <sub>C</sub> = +100°C	P <sub>D</sub>	41		
Thermal Resistance, Junction to Ambient (Note 6)		R <sub>0JA</sub>	41	°C/W	
Thermal Resistance, Junction to Case (Note 5)		R <sub>0</sub> JC	1.2	-C/VV	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C	

## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)	Oymbol		тур	Max	Onit	Test oblightion	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-450	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current	IDSS	_	_	-1	μA	$V_{DS} = -450V, V_{GS} = 0V$	
Gate-Source Leakage	Igss	—	—	±100	nA	$V_{GS} = \pm 30V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)	•					•	
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-3.0	-4.0	-5.0	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	3.1	4.9	Ω	V <sub>GS</sub> = -10V, I <sub>D</sub> = -1.05A	
Diode Forward Voltage	V <sub>SD</sub>		_	-1.4	V	$V_{GS} = 0V, I_{S} = -2.1A$	
Forward Transconductance	gfs	_	1.4	_	S	$V_{DS} = -50.0V, I_{D} = -1.05A$	
DYNAMIC CHARACTERISTICS (Note 7)	•						
Input Capacitance	Ciss		564	_		$V_{DS} = -25V, V_{GS} = 0V, f = 1.0MHz$	
Output Capacitance	Coss	_	70	_	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	_	3.3	_			
Total Gate Charge (V <sub>GS</sub> = -10V)	Qg	_	13.7	_		V <sub>DS</sub> = -360V, I <sub>D</sub> = -2.7A, V <sub>GS</sub> = -10V	
Gate-Source Charge	Q <sub>gs</sub>	_	3.4	_	nC		
Gate-Drain Charge	Q <sub>gd</sub>	_	6.0	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	21	_		$V_{DD}$ = -225V, $R_{G}$ = 3.0 $\Omega$ , $I_{D}$ = -2.7A	
Turn-On Rise Time	t <sub>R</sub>	_	54	_			
Turn-Off Delay Time	t <sub>D(OFF)</sub>		34		ns		
Turn-Off Fall Time	t <sub>F</sub>		34				
Body Diode Reverse Recovery Time	t <sub>RR</sub>		168		ns	$V_{GS} = 0V, V_{DD} = -200V, I_{S} = -2.7A,$	
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	—	1.3		μC	dI/dt = 100A/µs	

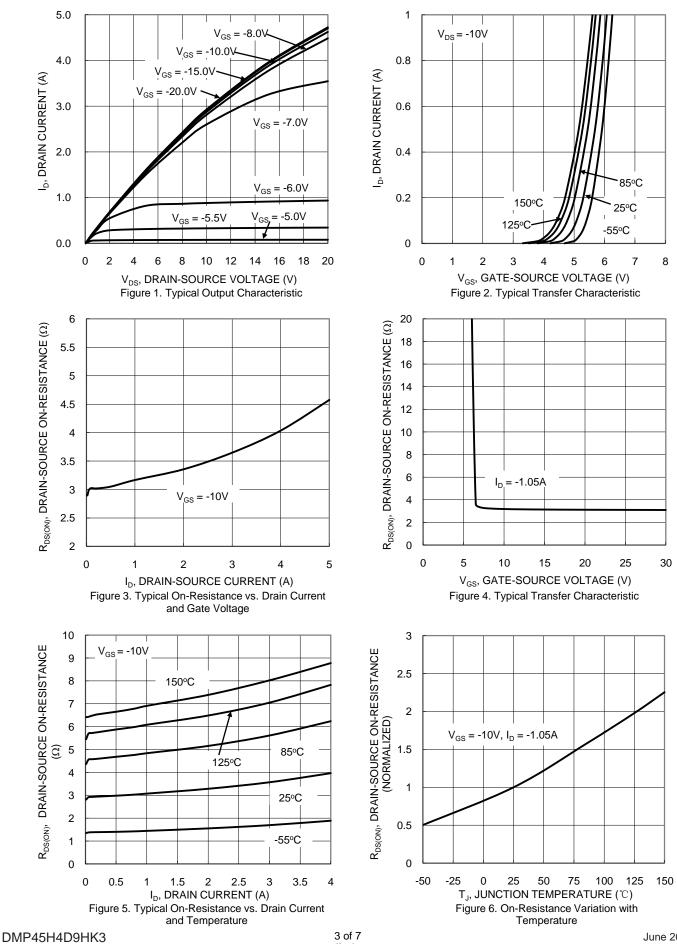
Notes: 5. Device mounted on infinite heatsink.

6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.

Guaranteed by design. Not subject to production testing.
Short duration pulse test used to minimize self-heating effect.



# DMP45H4D9HK3



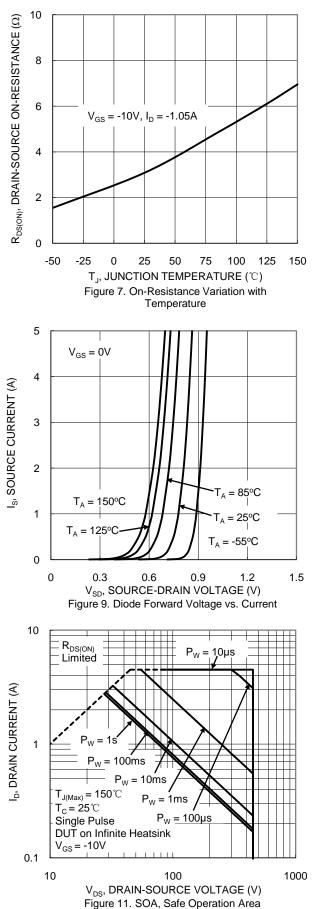
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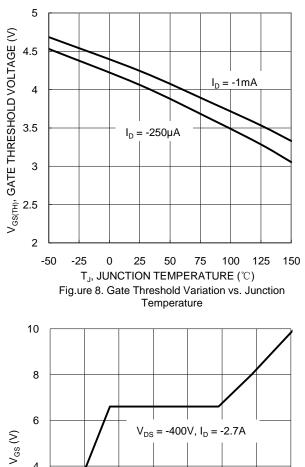
www.diodes.com

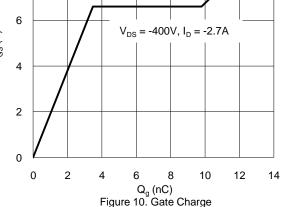
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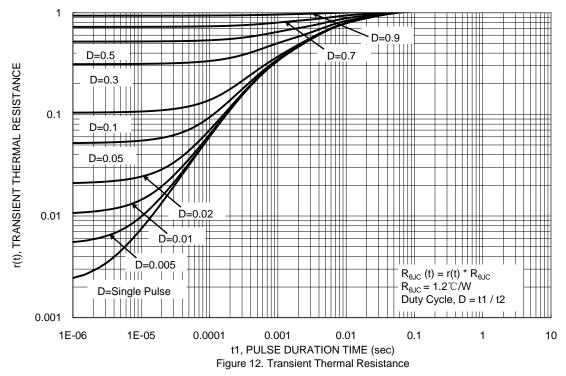
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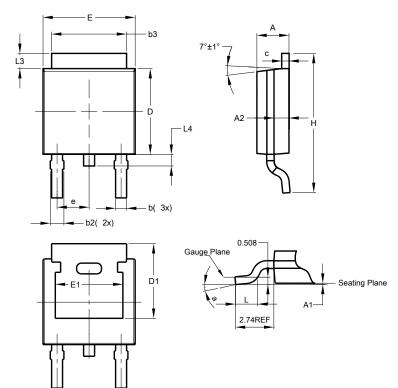




# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)

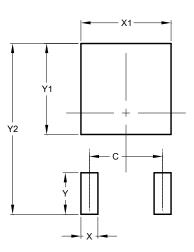


TO252 (DPAK)					
Dim	Min	Max	́Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)
С	4.572
Х	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700



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